

## Microstructure and Unusual Ferromagnetism of Epitaxial SnO<sub>2</sub> Films Implanted with Co Ions

Rustam I. Khaibullin <sup>1,2</sup>, Amir I. Gumarov <sup>1,2</sup>, Iskander R. Vakhitov <sup>1,2</sup>, Andrei A. Sukhanov<sup>1</sup>, Nikolay M. Lyadov <sup>1,2</sup>, Airat G. Kiiamov <sup>2</sup>, Dilyara M. Kuzina <sup>3</sup>, Valery V. Bazarov <sup>1</sup>, and Almaz L. Zinnatullin <sup>1,2,\*</sup>

<sup>1</sup> Zavoisky Physical-Technical Institute, FRC Kazan Scientific Centre of RAS, Kazan 420029, Russia

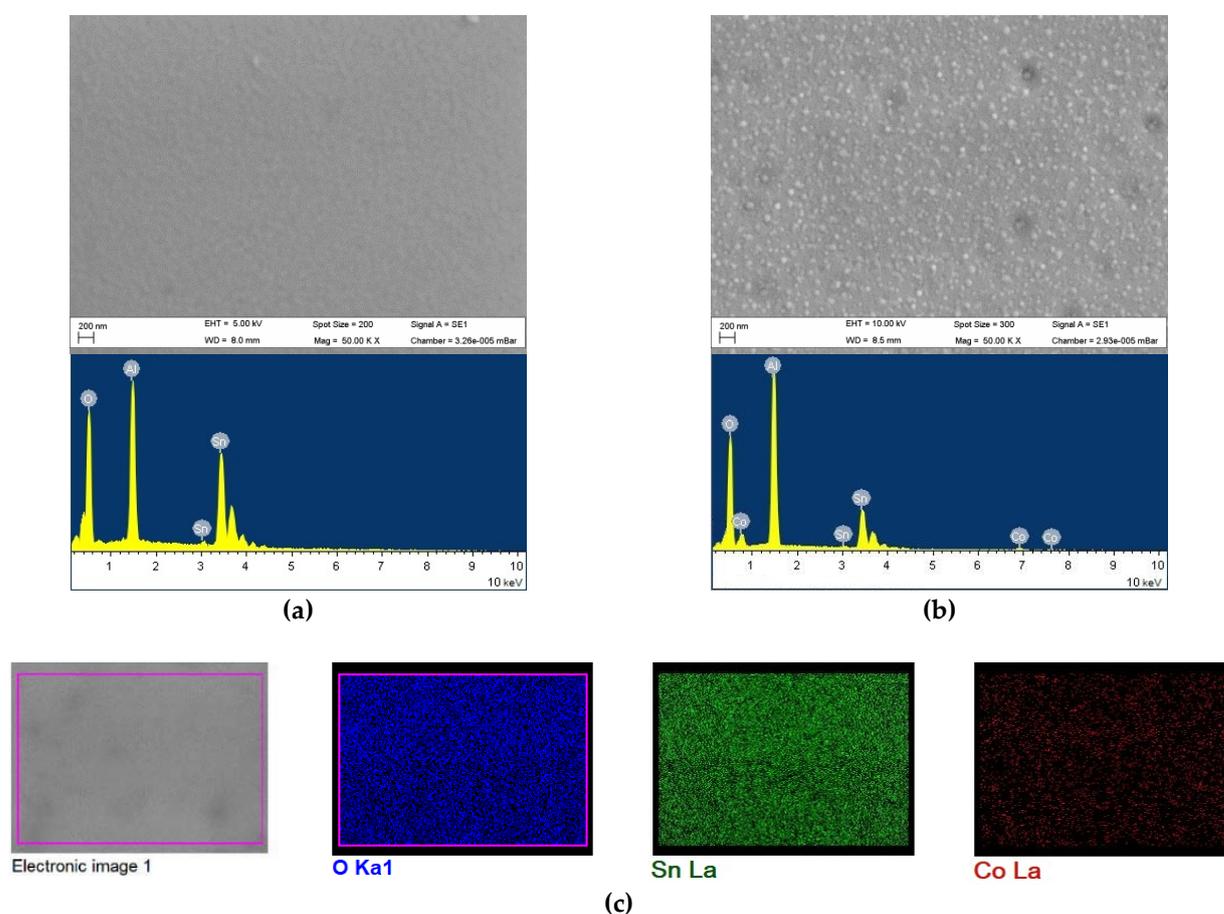
<sup>2</sup> Institute of Physics, Kazan Federal University, Kazan 420008, Russia

<sup>3</sup> Institute of Geology and Petroleum Technologies, Kazan Federal University, Kazan 420008, Russia

\* Correspondence: [almaz.zinnatullin@gmail.com](mailto:almaz.zinnatullin@gmail.com)

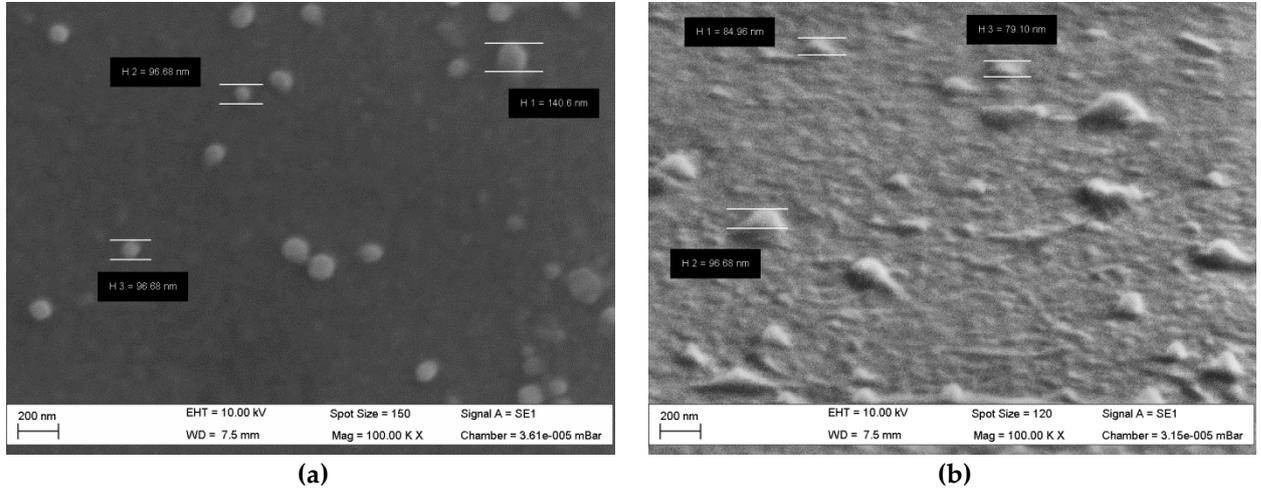
### 1. SEM study of both as-prepared and Co- (or Ar)-ions implanted SnO<sub>2</sub> films

The surface morphology and chemical element composition of SnO<sub>2</sub> samples were investigated utilizing an EVO 50 XVP scanning electron microscope (SEM) equipped with an energy dispersive X-ray (EDX) spectrometer (Oxford, Inca Energy 350). The SEM analysis of both the as-prepared and Co-ions implanted SnO<sub>2</sub> film is presented in **Figures S1**. The SEM images clearly illustrate that the surface of the SnO<sub>2</sub> films, upon intense ion irradiation, exhibits pronounced roughness along with the presence of blisters and neoplasms. The EDX spectrum confirms successful implantation of Co ions into the SnO<sub>2</sub> structure, and the EDX mapping reveals a homogeneous distribution of the cobalt implant at the submicron scale across the entire surface of the implanted SnO<sub>2</sub>.



**Figure S1.** SEM images of the surface of SnO<sub>2</sub> film before (a) and after (b) implantation with 40 keV Co<sup>+</sup> ions to the fluence of  $1.0 \times 10^{17}$  ion/cm<sup>2</sup>; (c) –EDX elemental mapping of the surface of the Co-ions implanted SnO<sub>2</sub> film at the submicron (20,000x magnification) scale.

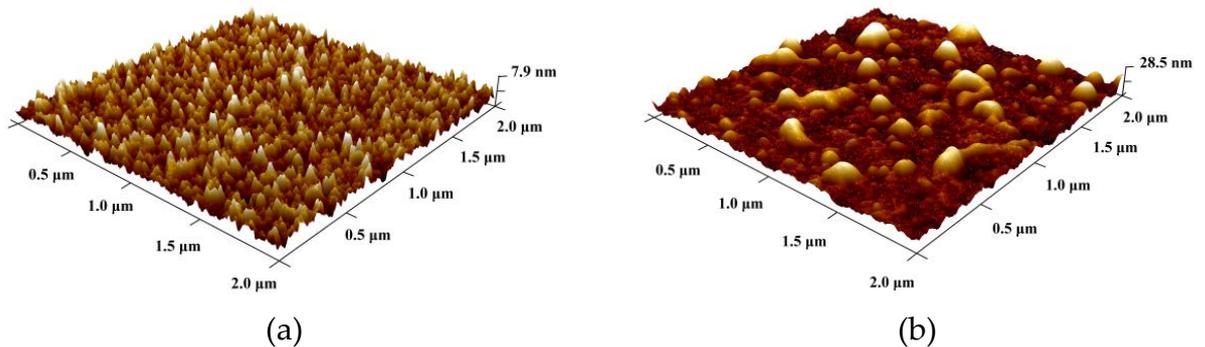
The similar picture is taken place in Ar-ions implanted SnO<sub>2</sub> film (see **Figure S2**). Here, the neoplasms with semi-spherical form are also observed on the surface of the film after intense irradiation with argon ions, but their surface density is lower than the density of new formations in films implanted with cobalt ions. Since the EDX spectrum of Ar-ions implanted SnO<sub>2</sub> film (not shown) reveals very weak energy peaks associated with argon, we can conclude that the most of chemically inert argon leaves the implanted SnO<sub>2</sub> film due to outward diffusion process.



**Figure S2.** SEM image of the surface of SnO<sub>2</sub> film after implantation with 40 keV Ar<sup>+</sup> ions to the fluence of  $1.0 \times 10^{17}$  ion/cm<sup>2</sup> (a) and SEM image of same film under 70° degrees with respect to electron beam (b).

## 2. AFM study of both as-prepared and Co-ions implanted SnO<sub>2</sub> films

Atomic force microscopy (AFM) study of the surface morphology of SnO<sub>2</sub> films was performed in addition to SEM study. The Dimension FastScan Bruker AFM has been used for this purpose. An AFM study of the surface morphology of as-prepared SnO<sub>2</sub> films (**Figure S3a**) showed that film surface is quite smooth with a roughness of 5-7 nm. On the contrary, AFM image presented in **Figure S3b** show that large neoplasms (~40-70 nm in sizes) are formed on the surface of the film after high-fluence implantation with Co ions.

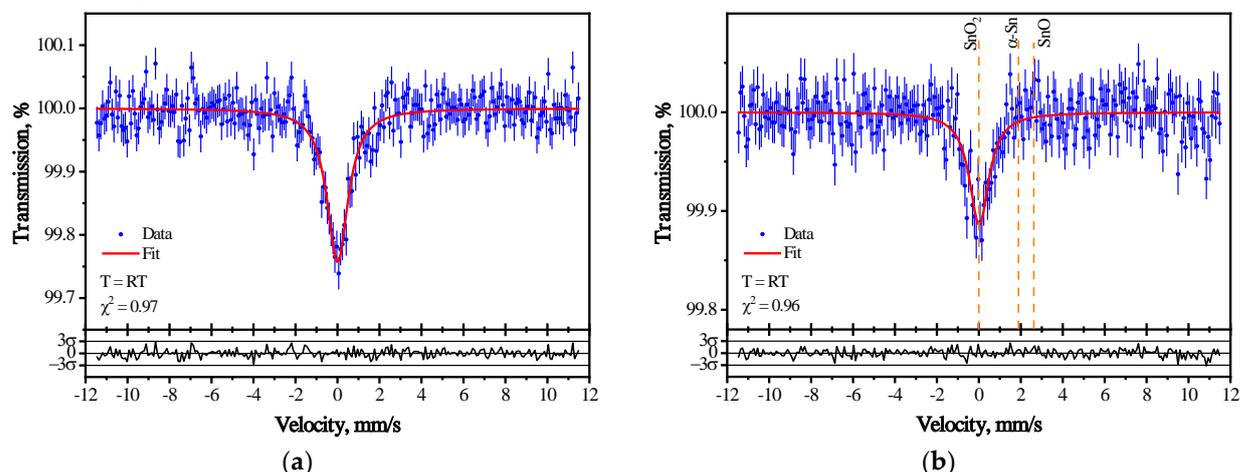


**Figure S3.** AFM images of the surface of SnO<sub>2</sub> film before (a) and after (b) implantation with 40 keV Co<sup>+</sup> ions to the fluence of  $1.0 \times 10^{17}$  ion/cm<sup>2</sup>.

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### 3. $^{119}\text{Sn}$ Mössbauer studies of the epitaxial $\text{SnO}_2$ film on C-cut $\text{Al}_2\text{O}_3$ substrate before and after Co ions implantation

Room-temperature transmission  $^{119}\text{Sn}$  Mössbauer studies were carried out using conventional WissEl spectrometer working in the constant acceleration mode.  $^{119\text{m}}\text{Sn}(\text{CaSnO}_3)$  source with an activity of about 15 mCi (RITVERC) was used. The spectrometer velocity scale was calibrated using thin metallic iron foil at room temperature. The spectra were least-squares fitted using SpectrRelax 2.1 software [1]. The values of isomer shifts are determined versus center of polycrystalline thin  $\text{SnO}_2$  absorber spectrum at room temperature.

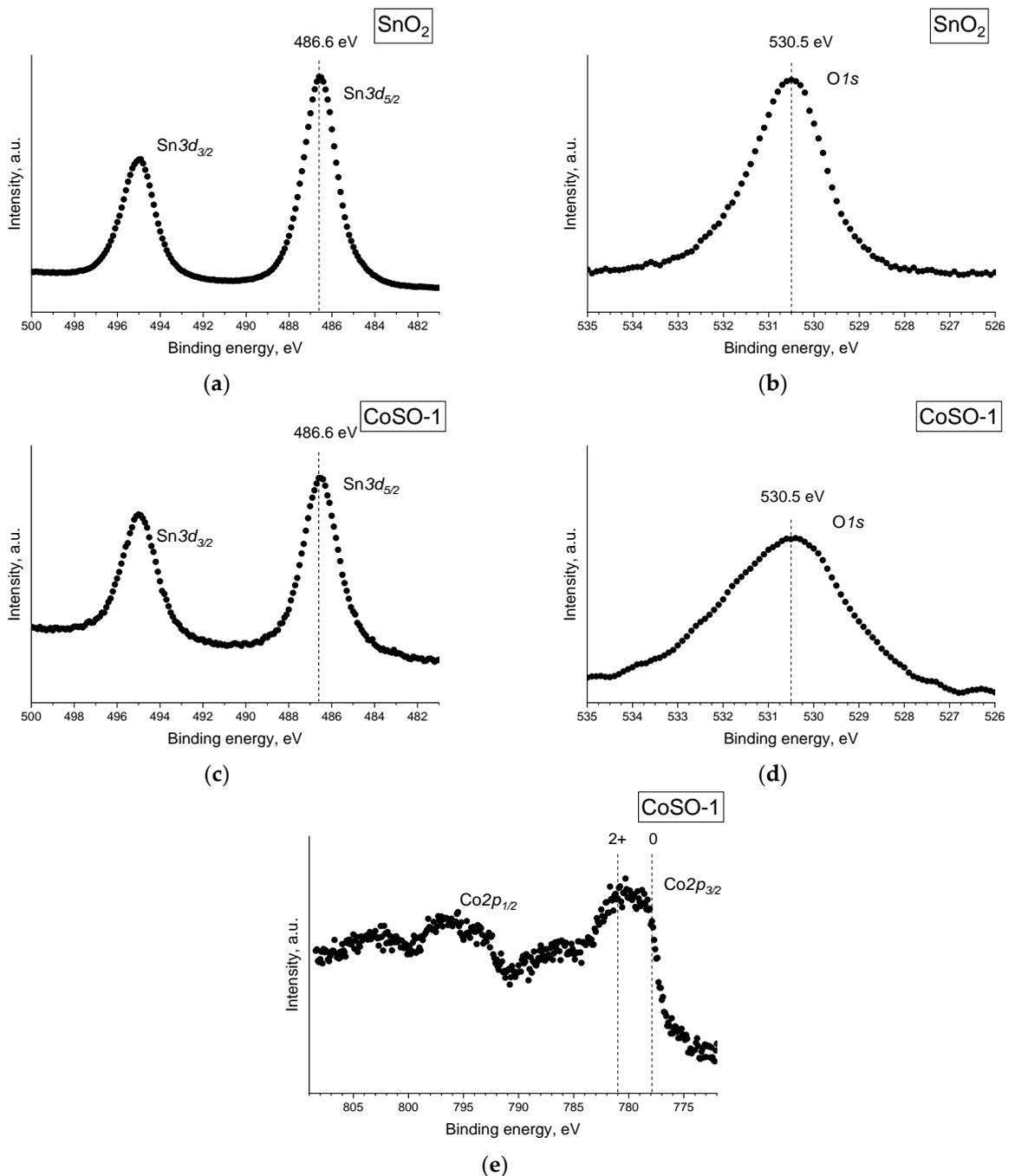


**Figure S4.**  $^{119}\text{Sn}$  Mössbauer spectra of the epitaxial  $\text{SnO}_2$  film on C-cut  $\text{Al}_2\text{O}_3$  substrate before (a) and after (b) the implantation with 40 keV  $\text{Co}^+$  ions with the fluence of  $1 \times 10^{17}$  ions/cm $^2$ . Blue points with statistical error bars represent the experimental spectra, whereas solid red curves – the best-fit results. In panel (b) the dashed orange lines show the isomer shift values for tin dioxide ( $\text{SnO}_2$ ), tin monoxide ( $\text{SnO}$ )  $\alpha$ -phase of metallic tin ( $\alpha\text{-Sn}$ ), respectively [2].

The results of  $^{119}\text{Sn}$  Mössbauer studies of the epitaxial  $\text{SnO}_2$  film on C-cut  $\text{Al}_2\text{O}_3$  substrate before implantation is shown in **Figure S4(a)**. The spectrum of the film in the initial state was the single absorption line with the isomer shift corresponding to the  $\text{Sn}^{4+}$  ions in  $\text{SnO}_2$ . After Co ions implantation, the spectrum did not change qualitatively (**Figure S4(b)**). It should be noted that within the experimental signal-to-noise ratio the additional components corresponding to the tin ions in other states were not observed. It proves that the Co ions implantation did not notably affect the valence state of tin atoms in the implanted  $\text{SnO}_2$  film.

### 4. High-resolution X-ray photoelectron spectra (XPS)

High-resolution XPS spectra were taken at room temperature by using a Phoibos 150 hemispherical energy analyzer (SPECS GmbH, Berlin, Germany). The obtained results were analyzed using CasaXPS software [3]. The experimental data both for as-prepared and Co-ions implanted  $\text{SnO}_2$  films are depicted in **Figure S5**. It was established that the valence states of tin and oxygen atoms are preserved under the Co ions implantation and the XPS peak positions correspond to  $\text{Sn}^{4+}$  and  $\text{O}^{2-}$  states. At the same time, Co implant was found in the mixed valence state: either in the form of metal atom  $\text{Co}^0$  or  $\text{Co}^{2+}$  ions. The detailed deconvolution of  $\text{Co}2p_{3/2}$  region into components is presented in the paper.



**Figure S5.** High resolution XPS spectra of  $\text{Sn}3d$  (a, c),  $\text{O}1s$  (b, d) and  $\text{Co}2p$  (e) in both as-prepared  $\text{SnO}_2$  film (a, b) and  $\text{SnO}_2$  film implanted with 40 keV  $\text{Co}^+$  ions to the fluence of  $1 \times 10^{17}$  ions/cm<sup>2</sup> (c, d, e).

## References

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